Amendments to the Specification:

Please replace the paragraph beginning at page 31, line 12 as with the following amended paragraph:

A source region **[[360]]** 340, a drain region **[[361]]** 341, and a Lov region 342, into which an impurity element having a conductivity type which is the inverse of the above single conductivity type, are then formed in the p-channel TFT forming semiconductor layer 302, as shown in Fig. 4C. The second shape conductive layer 320 is used as a mask with respect to the impurity element, and the impurity regions are formed in a self-aligning manner. The entire surfaces of the semiconductor layers 303 and 304, which form n-channel TFTs, are covered by a resist mask 343 at this point. Phosphorous is already added in differing concentrations to the source region **[[360]]** 340, the drain region **[[361]]** 341, and the Lov region 342, and ion doping is performed here using diborane (B_2H_6), so that boron is also added to each of the regions with a concentration of $2x10^{20}$ to $2x10^{21}$ atoms/cm^3. In practice, the boron contained in the source region **[[360]]** 340, the drain region **[[361]]** 341, and the Lov region 342 is influenced by the film thickness of the conductive layers and the insulating film, which have a tapered shape in cross section at their edge portions above the semiconductor layers, similar to the second doping process. The concentration of the impurity element added also changes.